

Form PTO-1449			U.S. Department of Commerce Patent and Trademark Office		Attorney Docket No. 5308-395	Serial No. <u>10/790406</u> To be assigned	
LIST OF DOCUMENTS CITED BY APPLICANT (Use several sheets if necessary)			Applicant: O'Loughlin et al. Filing Date: Concurrently herewith			GAU: Unknown	
<b>U.S. PATENT DOCUMENTS</b>							
Examiner Initials		Document No.	Date (m/d/y)	Name	Class	Subclass	Filing Date if Appropriate
<u>JU</u>	1	US2003/0079689A1	5/1/03	Sumakeris et al.	118	725	
<b>FOREIGN PATENT DOCUMENTS</b>							
		Document Number	Date	Country	Class	Subclass	Translation (Yes/No)
<b>OTHER DOCUMENTS</b>							
<u>JU</u>	2	Okada et al. "Crystallographic defects under surface morphological defects of 4H-SiC homoepitaxial films," ICSCRM 2003 Poster Sessions.					
<u>JU</u>	3	Wahab et al. "Influence of epitaxial growth and substrate-induced defects on the breakdown of 4H-SiC Schottky diodes," <i>Applied Physics Letters</i> , Vol. 76, No. 19, May 8, 2000, pp. 2725-7.					
<u>JU</u>	4	U.S. Application Serial No. 10/414,787 entitled <i>Methods and Apparatus for Controlling Formation of Deposits in a Deposition System and Deposition Systems and Methods Including the Same</i> , filed April 16, 2003.					
<u>JU</u>	5	U.S. Application Serial No. 09/756,548, titled <i>Gas Driven Rotation Apparatus and Method for Forming Silicon Carbide Layers</i> , filed January 8, 2001.					
<u>JU</u>	6	U.S. Application Serial No. 10/117,858, titled <i>Gas Driven Planetary Rotation Apparatus and Methods for Forming Silicon Carbide Layers</i> , filed April 8, 2002.					

Examiner: Ed Date Considered: 7/10/06

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